

TO-220 Plastic Package

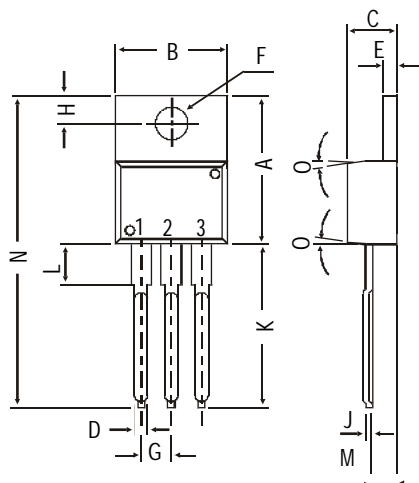
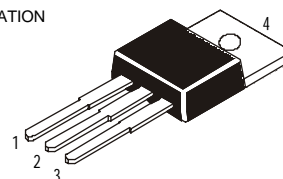
CSC1061

CSC1061 NPN PLASTIC POWER TRANSISTOR

Low frequency Power Amplifier

PIN CONFIGURATION

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR



All dimensions in mm.

DIM	MIN.	MAX.
A	14.42	16.51
B	9.63	10.67
C	3.56	4.83
D		0.90
E	1.15	1.40
F	3.75	3.88
G	2.29	2.79
H	2.54	3.43
J		0.56
K	12.70	14.73
L	2.80	4.07
M	2.03	2.92
N		31.24
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ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)

Collector-emitter voltage (open base)

Collector current

Total power dissipation up to $T_C = 25^\circ\text{C}$

Junction temperature

Collector-emitter saturation voltage

$I_C = 2\text{A}; I_B = 0.2\text{A}$

D.C. current gain

$I_C = 1\text{A}; V_{CE} = 4\text{V}$

V_{CBO} max. 50 V

V_{CEO} max. 50 V

I_C max. 3.0 A

P_{tot} max. 25 W

T_j max. 150 °C

V_{CEsat} max. 1.0 V

h_{FE} min. 35

max. 320

RATINGS (at $T_A=25^\circ\text{C}$ unless otherwise specified)

Limiting values

Collector-base voltage (open emitter)

Collector-emitter voltage (open base)

Emitter-base voltage (open collector)

Collector current

V_{CBO} max. 50 V

V_{CEO} max. 50 V

V_{EBO} max. 4.0 V

I_C max. 3.0 A

CSC1061

Total power dissipation up to $T_C = 25^\circ\text{C}$
 Junction temperature
 Storage temperature

P_{tot}	max.	25 W
T_j	max.	150 °C
T_{stg}		-65 to +150 °C

CHARACTERISTICS

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified

Collector cutoff current

$I_E = 0$; $V_{CB} = 20\text{V}$

I_{CBO}	max.	100 μA
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Breakdown voltages

$I_C = 50\text{ mA}$; $I_B = 0$

V_{CEO}	min.	50 V
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$I_C = 5\text{ mA}$; $I_E = 0$

V_{CBO}	min.	50 V
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$I_E = 5\text{ mA}$; $I_C = 0$

V_{EBO}	min.	4.0 V
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Saturation voltages

$I_C = 2\text{ A}$; $I_B = 0.2\text{ A}$

V_{CEsat}	max.	1.0 V
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Base emitter on voltage

$I_C = 1\text{ A}$; $V_{CE} = 4\text{ V}$

$V_{BE(on)}$	max.	1.5 V
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D.C. current gain

$I_C = 0.1\text{ A}$; $V_{CE} = 4\text{ V}$

h_{FE}	min.	35
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$I_C = 1\text{ A}$; $V_{CE} = 4\text{ V}^{**}$

h_{FE}	min.	35
	max.	320

Transition frequency

$I_C = 0.5\text{ A}$; $V_{CE} = 4\text{ V}$

f_T	typ.	8 MHz
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**** h_{FE} classification: A: 35-70 B: 60-120 C: 100-200 D: 160-320**

Customer Notes

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/ CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.

Telephone + 91-11-2579 6150, 5141 1112 Fax + 91-11-2579 5290, 5141 1119

email@cdil.com www.cdilsemi.com